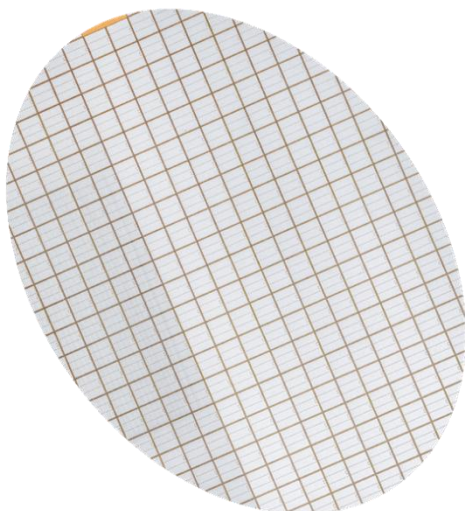


SIS0150C120i23

I23 micro pattern IGBT, 10.1 mm x 9.9 mm

精细沟槽栅 i23 IGBT 芯片, 10.1 mm x 9.9 mm

 $V_{CE} = 1200\text{ V}$ $I_C = 150\text{ A}$

- i23 ultra-low-loss micro pattern Trench IGBT chip-set
i23 超低损耗精细沟槽栅型 IGBT 芯片组
- Soft switching for a broad application range due to best turn-off controllability
由于具有最佳的关断可控性, 软开关适用于广泛的应用范围
- positive temperature coefficient
正温度系数
- easy paralleling
易并联

Maximum ratings¹ 最大额定值

PARAMETER 参数	SYMBOL 符号	CONDITIONS 工作条件	MIN 最小值	MAX 最大值	UNIT 单位
Collector-emitter voltage 集电极-发射极电压	V_{CES}	$V_{GE} = 0\text{ V}$, $T_{vj} \geq 25\text{ °C}$		1200	V
DC collector current 集电极直流电流	I_C			150	A
Peak collector current 集电极峰值电流	I_{CM}	t_p limited by $T_{vj\text{ max}}$ 脉冲宽度依据 $T_{vj\text{ max}}$ 设定		300	A
Gate-emitter voltage 栅极-发射极驱动电压	V_{GES}		-20	20	V
Junction temperature 结温	T_{vj}		-40	175	°C
Junction operating temperature 运行结温	$T_{vj(op)}$		-40	175	°C
Short circuit ² 短路	t_{sc}	$V_{GE} = 15\text{ V}$, $V_{CC} = 800\text{ V}$, $T_{vj} = 175\text{ °C}$ ³		8	μs



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¹ Maximum rated values indicate limits beyond which damage to the device may occur per IEC 60747¹ 根据标准 IEC 60747 要求, 最大额定值表示超过该限值可能会对器件造成损坏² Not subject to production test, capability depending on module design² 不从属于生产测试, 性能取决于模块设计³ Short circuit performance at high temperature requires suitable die assembly process³ 高温下的短路性能测试, 需要合适的芯片封装工艺。



IGBT⁴

PARAMETER 参数	SYMBOL 符号	CONDITIONS 条件	MIN 最小	TYP 典型	MAX 最大	UNIT 单位
Collector(-emitter) breakdown voltage 集电极-发射极击穿电压	$V_{(BR)CES}$	$V_{GE} = 0\text{ V}$, $I_C = 0.25\text{ mA}$, $T_{vj} = 25\text{ °C}$	1200			V
Collector-emitter saturation voltage ⁵ 集电极-发射极饱和电压	V_{CESat}	$I_C = 150\text{ A}$, $V_{GE} = 15\text{ V}$	$T_{vj} = 25\text{ °C}$	1.55		V
			$T_{vj} = 125\text{ °C}$	1.80		V
			$T_{vj} = 175\text{ °C}$	1.85		V
Collector cut-off current 集电极截止电流	I_{CES}	$V_{CE} = 1200\text{ V}$, $V_{GE} = 0\text{ V}$	$T_{vj} = 25\text{ °C}$		1	μA
Gate leakage current 栅极漏电流	I_{GES}	$V_{CE} = 0\text{ V}$, $V_{GE} = \pm 20\text{ V}$	-0.1		0.1	μA
Gate-emitter threshold voltage 栅极-发射极阈值电压	$V_{GE(th)}$	$I_C = 7.5\text{ mA}$, $V_{CE} = V_{GE}$, $T_{vj} = 25\text{ °C}$		6.3		V
Gate charge 栅极电荷	Q_G	$I_C = 150\text{ A}$, $V_{CE} = 600\text{ V}$, $V_{GE} = -15\text{ V}$, 15 V		1.33		μC
Input capacitance 输入电容	C_{ies}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 100\text{ kHz}$, $T_{vj} = 25\text{ °C}$		20.4		nF
Output capacitance 输出电容	C_{oes}			460		pF
Reverse transfer capacitance 反向传输电容	C_{res}			190		pF
Internal gate resistor 栅极内阻	R_{Gint}	Per switch 每个芯片		2.6		Ω
Turn-on delay time 开通延迟	$t_{d(on)}$	$V_{CC} = 600\text{ V}$, $I_C = 150\text{ A}$, $R_G = 3.0\text{ }\Omega$, $V_{GE} = \pm 15\text{ V}$	$T_{vj} = 25\text{ °C}$	195		ns
			$T_{vj} = 125\text{ °C}$	215		ns
			$T_{vj} = 175\text{ °C}$	220		ns
Rise time 上升时间	t_r		$T_{vj} = 25\text{ °C}$	65		ns
			$T_{vj} = 125\text{ °C}$	70		ns
			$T_{vj} = 175\text{ °C}$	80		ns
Turn-off delay time 关断延迟	$t_{d(off)}$	$V_{CC} = 600\text{ V}$, $I_C = 150\text{ A}$, $R_G = 3.0\text{ }\Omega$, $V_{GE} = \pm 15\text{ V}$	$T_{vj} = 25\text{ °C}$	160		ns
			$T_{vj} = 125\text{ °C}$	200		ns
			$T_{vj} = 175\text{ °C}$	250		ns
Fall time 下降时间	t_f		$T_{vj} = 25\text{ °C}$	380		ns
			$T_{vj} = 125\text{ °C}$	510		ns
			$T_{vj} = 175\text{ °C}$	530		ns
Turn-on switching energy 开通损耗	E_{on}	$V_{CC} = 600\text{ V}$, $I_C = 150\text{ A}$, $R_G = 3.0\text{ }\Omega$, $V_{GE} = \pm 15\text{ V}$ Diode: SID0150C120d20	$T_{vj} = 25\text{ °C}$	17.5		mJ
			$T_{vj} = 125\text{ °C}$	22		mJ
			$T_{vj} = 175\text{ °C}$	25		mJ
Turn-off switching energy 关断损耗	E_{off}	$V_{CC} = 600\text{ V}$, $I_C = 150\text{ A}$, $R_G = 3\text{ }\Omega$, $V_{GE} = \pm 15\text{ V}$	$T_{vj} = 25\text{ °C}$	14		mJ
			$T_{vj} = 125\text{ °C}$	19		mJ
			$T_{vj} = 175\text{ °C}$	21		mJ
Short circuit current 短路电流	I_{SC}	$t_{PCS} \leq 8\text{ }\mu\text{s}$, $V_{GE} = 15\text{ V}$, $T_{vj} = 175\text{ °C}$, $V_{CC} = 800\text{ V}$, $V_{CEM\text{ Chip}} \leq 1200\text{ V}$		815		A

⁴ Characteristic values according to IEC 60747-9

⁴ IGBT 特征数值均参考标准 IEC 60747-9



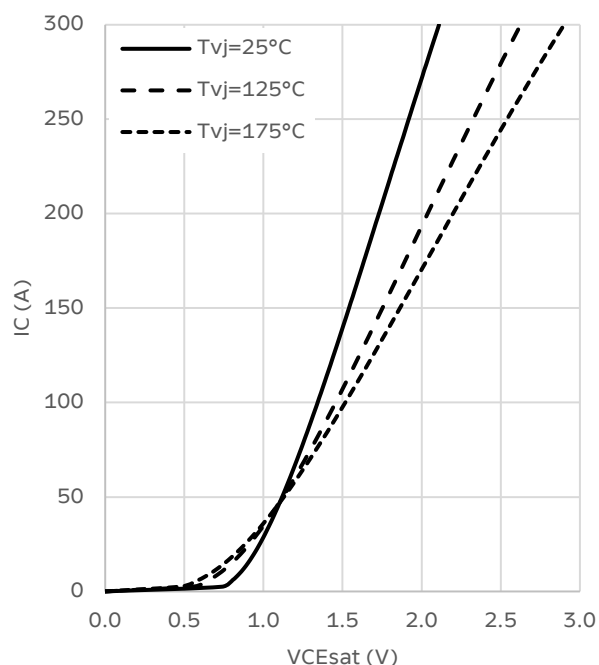
Characteristics 特性曲线

IGBT on-state characteristics (typical)

IGBT 通态特性曲线 (典型)

$I_C = f(V_{CE})$

$V_{GE} = 15\text{ V}$

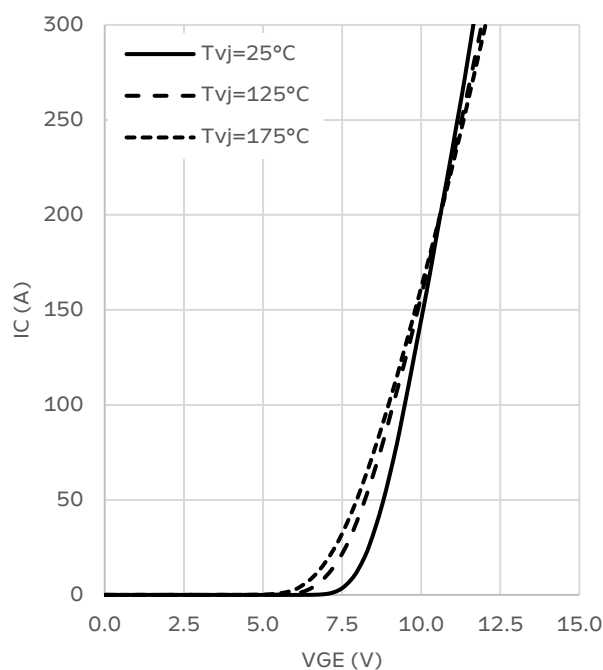


IGBT transfer characteristics (typical)

IGBT 转移特性曲线 (典型)

$I_C = f(V_{GE})$

$V_{CE} = 20\text{ V}$

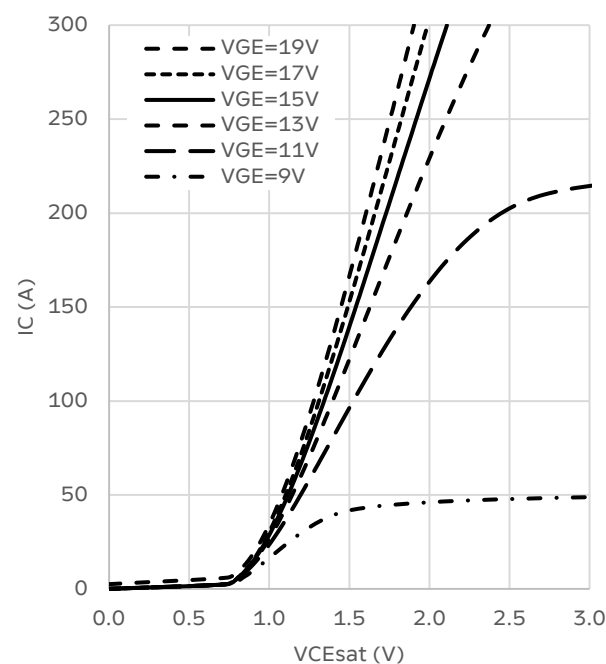


IGBT output characteristics (typical)

IGBT 输出特性曲线 (典型)

$I_C = f(V_{CE})$

$T_{vj} = 25^\circ\text{C}$

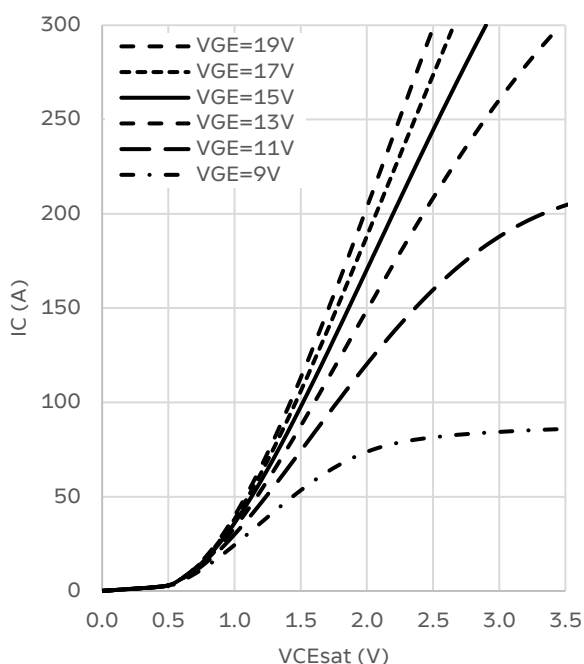


IGBT output characteristics (typical)

IGBT 输出特性曲线 (典型)

$I_C = f(V_{CE})$

$T_{vj} = 175^\circ\text{C}$



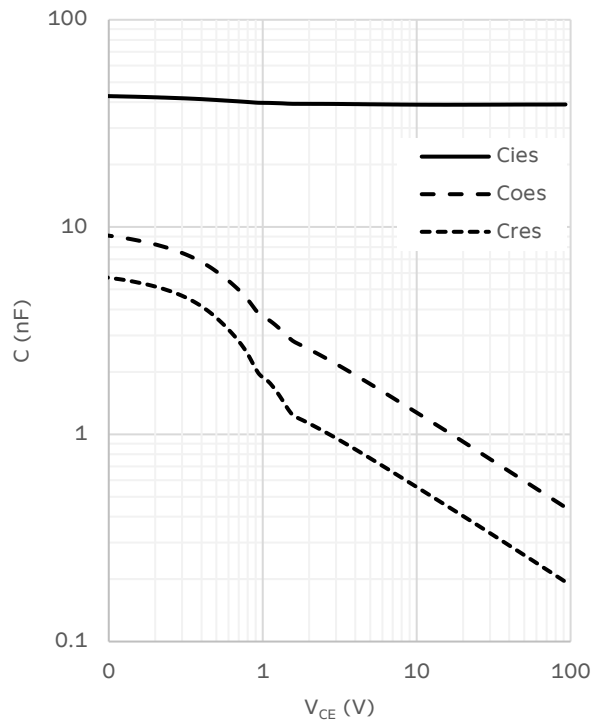


IGBT Capacitance characteristics (typical)

IGBT 电容特性曲线 (典型)

$C = f(V_{CE})$, $T_{vj} = 25\text{ }^{\circ}\text{C}$

$f = 100\text{ kHz}$, $V_{GE} = 0\text{ V}$

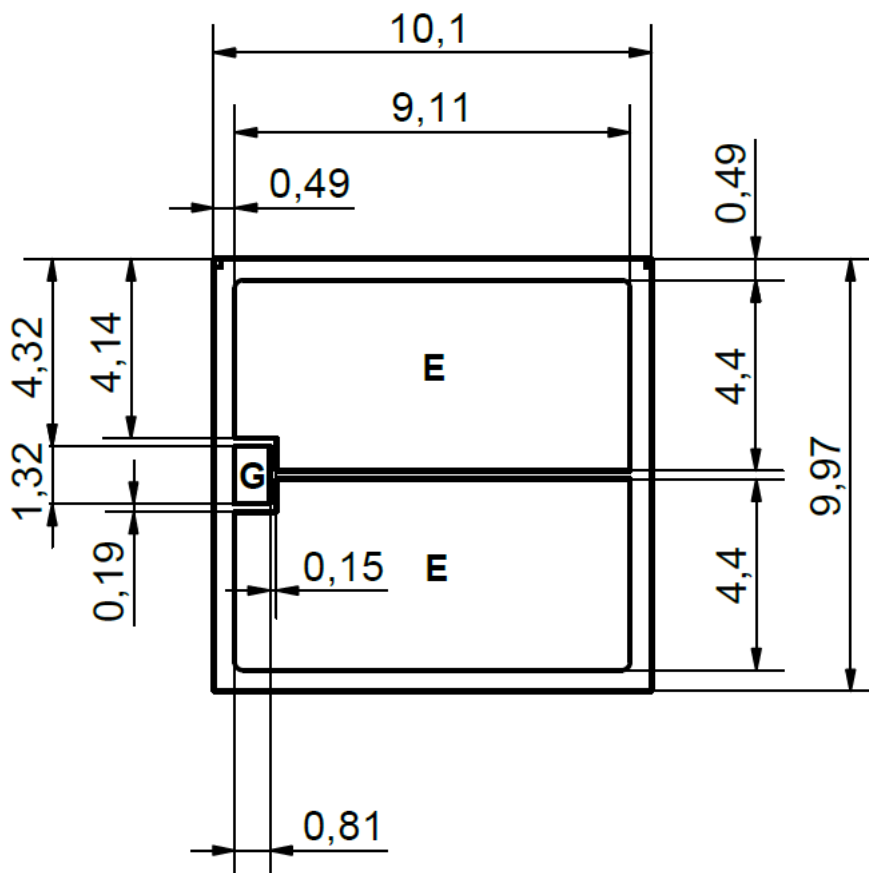




Mechanical properties⁶ 机械特性

PARAMETER 参数		UNIT 单位
Die size 芯片面积	(10.1± 0.01) x (9.97± 0.01)	mm ²
Gate pad size 栅极焊盘尺寸	1.32 x 0.81	mm ²
Thickness 厚度	135± 5	µm
Wafer diameter 晶圆直径	300	mm
Maximum chips per wafer 每片晶圆的最大芯片数	605	pcs
Frontside passivation 正面钝化层	Polyimide	
Frontside metal (pads) 正面金属 (衬垫)	Al Cu, 5000nm	
Backside metal 背面金属	Al Ni Ag System, 1100nm	

Chip drawing 芯片图



This is an electrostatic sensitive device.
此为静电敏感器件。

Ordering Information 订购信息

Part Number 零件编号	SIS0150C120i23
Package 包裹	Bare Die 裸露那些
Packaging Method 包装方式	Wafer 晶圆